UNISONIC TECHNOLOGIES CO., LTD

UFR8060C

FAST RECOVERY EPITAXIAL DIODE

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

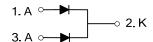
■ DESCRIPTION

The UTC **UFR8060C** utilizes advanced processing techniques to achieve ultrafast recovery times and higher forward current. Its soft recovery characteristics and high reliability suit for wide industrial applications.

■ FEATURES

- * Ultrafast Recovery Time
- * Soft Recovery Characteristics
- * Low Recovery Loss
- * Low Forward Voltage
- * High Surge Current Capability
- * Low Leakage Current

■ SYMBOL

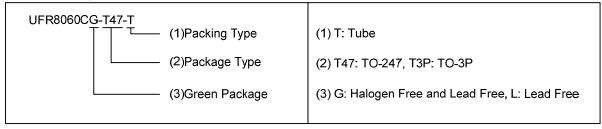


TO-247 TO-3P

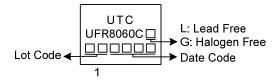
ORDERING INFORMATION

Ordering Number		Dealtes	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UFR8060CL-T47-T	UFR8060CG-T47-T	TO-247	Α	K	Α	Tube	
UFR8060CL-T3P-T	UFR8060CG-T3P-T	TO-3P	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Cathode



MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Maximum D.C. Reverse Voltage		V_R	600	>
Maximum Peak Repetitive Reverse Voltage		V_{RRM}	600	>
Maximum Working Peak Reverse Voltage		V_{RWM}	600	>
Maximum Average Forward Current	Per Leg		40	Α
(T _C =110°C)	Total	I _{F(AV)}	80	Α
Non-Repetitive Forward Surge Current (T _J =45°C, t=10ms, 50Hz, Sine)		I _{FSM}	330	А
Operating Temperature Range		TJ	-40 ~ +150	°C
Storage Temperature Range		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

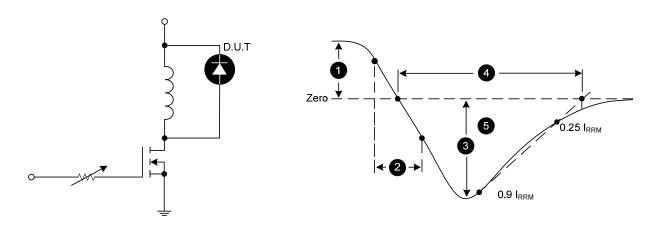
■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Case	θ_{JC}	0.8	°C/W	

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
STATIC PARAMETERS								
Forward Voltors	V _F	I _F =40A			2.0	V		
Forward Voltage		I _F =40A, T _J =150°C			1.8	V		
Maximum Davana Laglaga Cumant	I _{RM}	V _R =600V			100	μΑ		
Maximum Reverse Leakage Current		V _R =600V, T _J =150°C			500	μΑ		
DYNAMIC PARAMETERS								
Reverse Recovery Time	t _{rr}	I _F =1A, di _F /dt=-100A/μs, V _R =400V		64	80	ns		
Reverse Recovery Time	t _{rr}	I _F =30A, di _F /dt=-100A/μs, V _R =400V, T _J =25°C		85	105	ns		

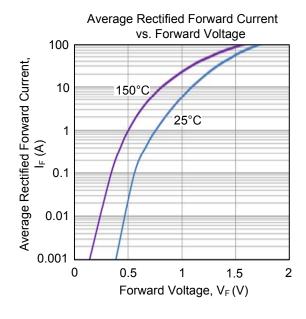
■ TEST CIRCUITS AND WAVEFORMS

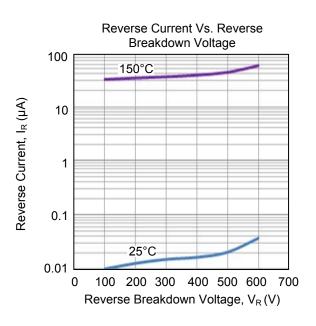


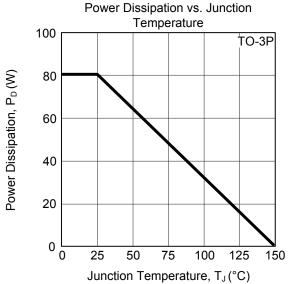
Diode Reverse Recovery Test Circuit and Waveform

- 1. I_F Forward Conduction Current
- 2. di_F/dt Rate of Diode Current Change Through Zero Crossing.
- 3. I_{RRM} Maximum Reverse Recovery Current.
- 4. t_{rr} Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5. Qrr Area Under the Curve Defined by I_{RRM} and $t_{\text{rr}}.$

■ TYPICAL CHARACTERISTICS







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